EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1312	(metal adj layer) with silicid$6 with anneal$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 08:17
L2	158	1 and ((dope$4 or implant$5) ion transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:05
L3	24	2 and inhibit$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:09
L4	5	2 and (inhibit$4 adj2 ion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 08:33
L8	1312	((metal adj layer) with silicid$6 with anneal$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 08:56
L9	16	L8 and (remov$4 unsilicid$4 metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/09 08:56
L10	3	9 and ((dope$4 or implant$5) (ion or $2nitrogen or hydrogen or fluorine) transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:14
L11	1	2 and ((dope$4 or implant$5) inhibit$4 (ion or $2nitrogen or hydrogen or fluorine) transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:04
L12	1631621	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:07

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L13	187	12 and (metal inhibit$4 silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:54
L14	20	13 and ((dope$4 or implant$5) (ion or $2nitrogen or hydrogen or fluorine) transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:56
L15	1637	12 and (metal (prevent or inhibit$4) silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:55
L16	2270	12 and (metal (prevent$4 or inhibit$4) silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:55
L17	259	16 and ((dope$4 or implant$5) (ion or $2nitrogen or hydrogen or fluorine) transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:56
L18	163	17 and anneal$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:56

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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1312	(metal adj layer) with silicid$6 with anneal$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 08:17
L2	158	1 and ((dope$4 or implant$5) ion transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:05
L3	24	2 and inhibit$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:09
L4	5	2 and (inhibit$4 adj2 ion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 08:33
L8	1312	((metal adj layer) with silicid$6 with anneal$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 08:56
L9	16	L8 and (remov$4 unsilicid$4 metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/09 08:56
L10	3	9 and ((dope$4 or implant$5) (ion or $2nitrogen or hydrogen or fluorine) transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:14
L11	1	2 and ((dope$4 or implant$5) inhibit$4 (ion or $2nitrogen or hydrogen or fluorine) transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:04
L12	1631621	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:07

EAST Search History

L13	187	12 and (metal inhibit$4 silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:10
L14	20	13 and ((dope$4 or implant$5) (ion or $2nitrogen or hydrogen or fluorine) transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/09 09:14

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	769062	transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 10:51
S2	5900	transistor with (metal adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 10:53
S3	68	transistor with ((metal adj layer) with silicid$6 with anneal$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 10:57
S4	1281	((metal adj layer) with silicid$6 with anneal$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 10:58
S5	15	S4 and (remov$4 unsilicid$4 metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/09 08:56
S6	11	S5 and (ion implant$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/26 11:46
S7	12	S5 and (ion near3 implant$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/26 11:47
S8	7	S4 and (remov$4 unsilicid$4 metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/01/26 11:47
S9	5	S8 and (ion near3 implant$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/27 09:39

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S10	5280	438/592,682,527,530,597,301.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/27 09:40
S11	490	S10 and (silicid$6 near3 anneal$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/27 09:42
S12	411	S11 and implant$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/27 09:43
S13	31	S12 and (transistor with (metal adj layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/27 09:46
S14	12	S12 and (transistor with substrate with (metal adj layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/27 09:46
S15	69	transistor with (metal adj layer) with silicid$6 with anneal$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 15:24
S16	1309	(metal adj layer) with silicid$6 with anneal$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 08:17
S17	618	(deposit metal transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/08 15:25
S20	4	S17 and (silicid$5 with (low adj temperature))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/03/08 15:29